



**SDI FINAL EVALUATION FORM 1.1**

**PART 1:**

Journal Name:	<a href="#">Physical Science International Journal</a>
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

**PART 2:**

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
<p>There is a thesis on that topic,          "Simulation and Characterization of Silicon Carbide Power Bipolar Junction Transistors" BENEDETTO BUONO Doctoral Thesis Stockholm, Sweden,          Is he same person with the author? Please confirm ethical issue that author obey ethical rules! What is the difference of his study from this thesis?</p>	

**Reviewer Details:**

Name:	Anonymous
Department, University & Country	Ege University, Turkey